

## Dual N-Channel 20 V (D-S) MOSFET

### PRODUCT SUMMARY

| $V_{DS}$ (V) | $R_{DS(on)}$ ( $\Omega$ ) | $I_D$ (A) |
|--------------|---------------------------|-----------|
| 20           | 0.280 at $V_{GS} = 4.5$ V | 1.28      |
|              | 0.360 at $V_{GS} = 2.5$ V | 1.13      |
|              | 0.450 at $V_{GS} = 1.8$ V | 1.0       |

### FEATURES

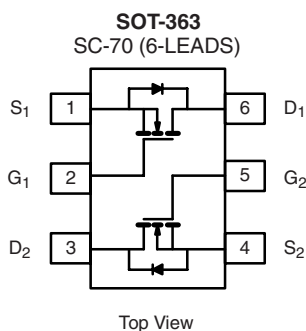
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs: 1.8 V Rated
- ESD Protected: 2000 V
- Thermally Enhanced SC-70 Package
- Compliant to RoHS Directive 2002/95/EC



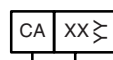
**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- Load Switching
- PA Switch
- Level Switch

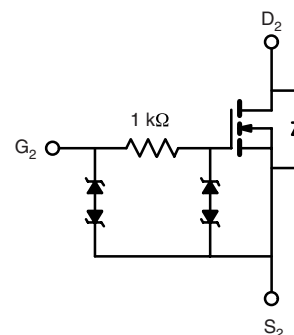
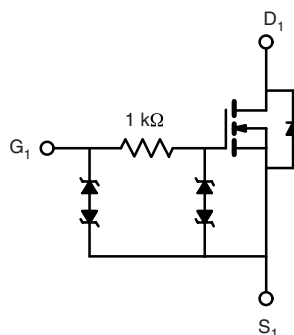


Marking Code



Lot Traceability  
and Date Code

Part # Code



**Ordering Information:** Si1912EDH-T1-E3 (Lead (Pb)-free)

Si1912EDH-T1-GE3 (Lead (Pb)-free and Halogen-free)

### ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

| Parameter                                                       |                        | Symbol                            | 5 s         | Steady State | Unit |
|-----------------------------------------------------------------|------------------------|-----------------------------------|-------------|--------------|------|
| Drain-Source Voltage                                            |                        | V <sub>DS</sub>                   | 20          |              | V    |
| Gate-Source Voltage                                             |                        | V <sub>GS</sub>                   | ± 12        |              |      |
| Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup> | T <sub>A</sub> = 25 °C | I <sub>D</sub>                    | 1.28        | 1.13         | A    |
|                                                                 | T <sub>A</sub> = 85 °C |                                   | 0.92        | 0.81         |      |
| Pulsed Drain Current                                            |                        | I <sub>DM</sub>                   | 4           |              |      |
| Continuous Diode-Current (Diode Conduction) <sup>a</sup>        |                        | I <sub>S</sub>                    | 0.61        | 0.48         |      |
| Maximum Power Dissipation <sup>a</sup>                          | T <sub>A</sub> = 25 °C | P <sub>D</sub>                    | 0.74        | 0.57         | W    |
|                                                                 | T <sub>A</sub> = 85 °C |                                   | 0.38        | 0.30         |      |
| Operating Junction and Storage Temperature Range                |                        | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 150 |              | °C   |

### THERMAL RESISTANCE RATINGS

| Parameter                                | Symbol     | Typical | Maximum | Unit |
|------------------------------------------|------------|---------|---------|------|
| Maximum Junction-to-Ambient <sup>a</sup> | $R_{thJA}$ | 130     | 170     | °C/W |
|                                          |            | 170     | 220     |      |
| Maximum Junction-to-Foot (Drain)         | $R_{thJF}$ | 80      | 100     |      |

Notes:

a. Surface mounted on 1" x 1" FR4 board.

**SPECIFICATIONS**  $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted

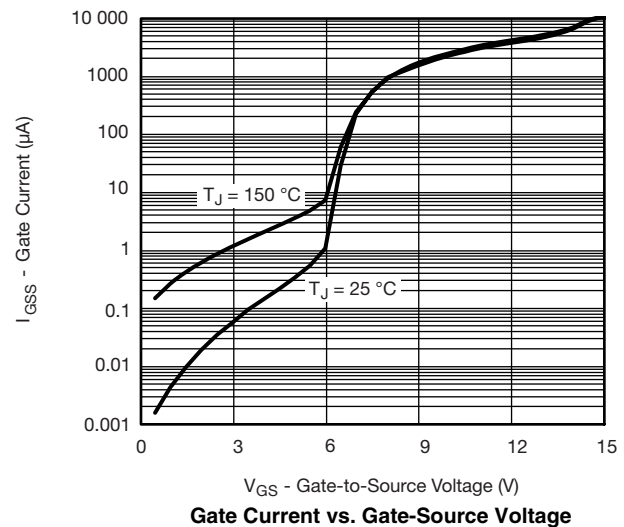
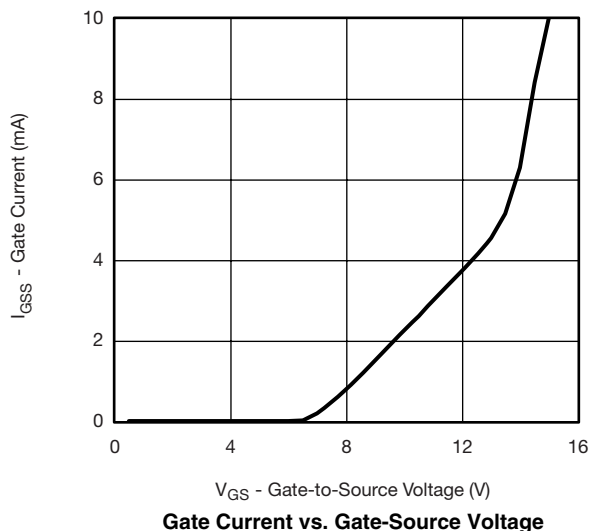
| Parameter                                     | Symbol       | Test Conditions                                                                                                                    | Min. | Typ.  | Max.     | Unit          |
|-----------------------------------------------|--------------|------------------------------------------------------------------------------------------------------------------------------------|------|-------|----------|---------------|
| <b>Static</b>                                 |              |                                                                                                                                    |      |       |          |               |
| Gate Threshold Voltage                        | $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 100\text{ }\mu\text{A}$                                                                                 | 0.45 |       |          | V             |
| Gate-Body Leakage                             | $I_{GSS}$    | $V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 4.5\text{ V}$                                                                                |      |       | $\pm 1$  | $\mu\text{A}$ |
|                                               |              | $V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 12\text{ V}$                                                                                 |      |       | $\pm 10$ | $\text{mA}$   |
| Zero Gate Voltage Drain Current               | $I_{DSS}$    | $V_{DS} = 16\text{ V}$ , $V_{GS} = 0\text{ V}$                                                                                     |      |       | 1        | $\mu\text{A}$ |
|                                               |              | $V_{DS} = 16\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 85\text{ }^{\circ}\text{C}$                                                |      |       | 5        |               |
| On-State Drain Current <sup>a</sup>           | $I_{D(on)}$  | $V_{DS} = 5\text{ V}$ , $V_{GS} = 4.5\text{ V}$                                                                                    | 2    |       |          | A             |
| Drain-Source On-State Resistance <sup>a</sup> | $R_{DS(on)}$ | $V_{GS} = 4.5\text{ V}$ , $I_D = 1.13\text{ A}$                                                                                    |      | 0.220 | 0.280    | $\Omega$      |
|                                               |              | $V_{GS} = 2.5\text{ V}$ , $I_D = 0.99\text{ A}$                                                                                    |      | 0.281 | 0.360    |               |
|                                               |              | $V_{GS} = 1.8\text{ V}$ , $I_D = 0.2\text{ A}$                                                                                     |      | 0.344 | 0.450    |               |
| Forward Transconductance <sup>a</sup>         | $g_{fs}$     | $V_{DS} = 10\text{ V}$ , $I_D = 1.13\text{ A}$                                                                                     |      | 2.6   |          | S             |
| Diode Forward Voltage <sup>a</sup>            | $V_{SD}$     | $I_S = 0.48\text{ A}$ , $V_{GS} = 0\text{ V}$                                                                                      |      | 0.8   | 1.2      | V             |
| <b>Dynamic<sup>b</sup></b>                    |              |                                                                                                                                    |      |       |          |               |
| Total Gate Charge                             | $Q_g$        | $V_{DS} = 10\text{ V}$ , $V_{GS} = 4.5\text{ V}$ , $I_D = 1.13\text{ A}$                                                           |      | 0.65  | 1        | nC            |
| Gate-Source Charge                            | $Q_{gs}$     |                                                                                                                                    |      | 0.2   |          |               |
| Gate-Drain Charge                             | $Q_{gd}$     |                                                                                                                                    |      | 0.23  |          |               |
| Turn-On Delay Time                            | $t_{d(on)}$  | $V_{DD} = 10\text{ V}$ , $R_L = 20\text{ }\Omega$<br>$I_D \cong 0.5\text{ A}$ , $V_{GEN} = 4.5\text{ V}$ , $R_g = 6\text{ }\Omega$ |      | 45    | 70       | ns            |
| Rise Time                                     | $t_r$        |                                                                                                                                    |      | 85    | 130      |               |
| Turn-Off Delay Time                           | $t_{d(off)}$ |                                                                                                                                    |      | 350   | 530      |               |
| Fall Time                                     | $t_f$        |                                                                                                                                    |      | 210   | 320      |               |

## Notes

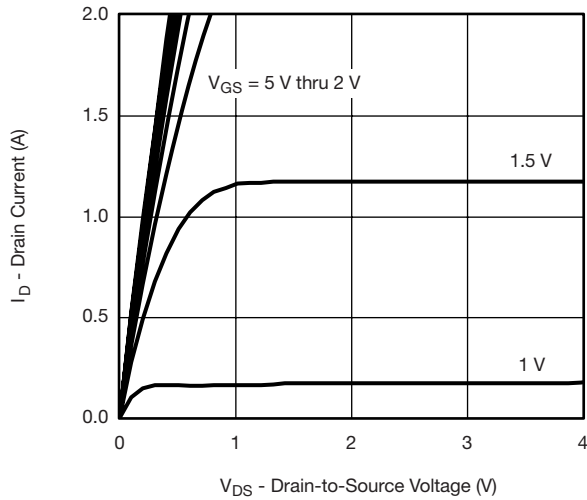
a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ 

b. Guaranteed by design, not subject to production testing.

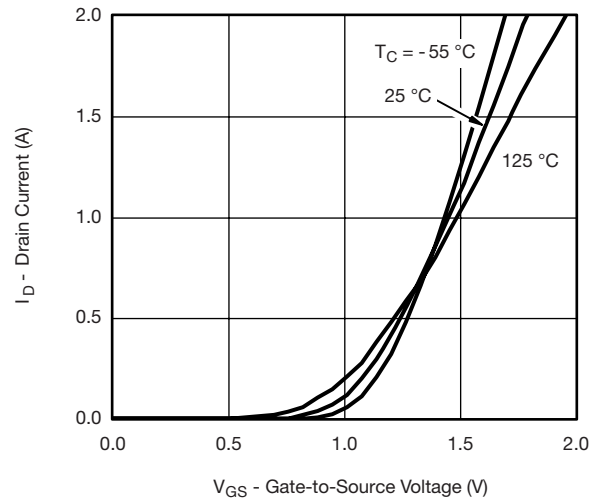
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS**  $25\text{ }^{\circ}\text{C}$ , unless otherwise noted

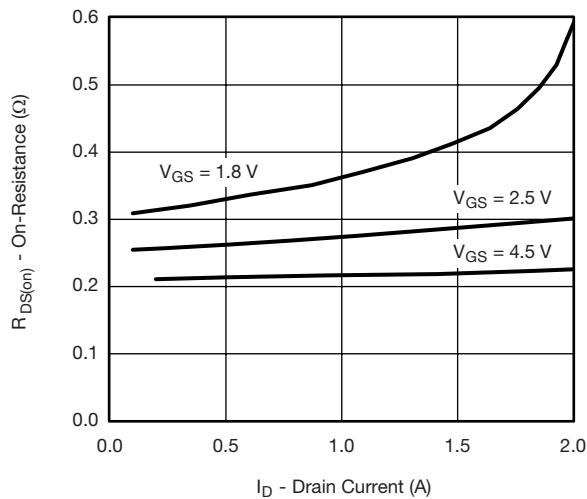
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



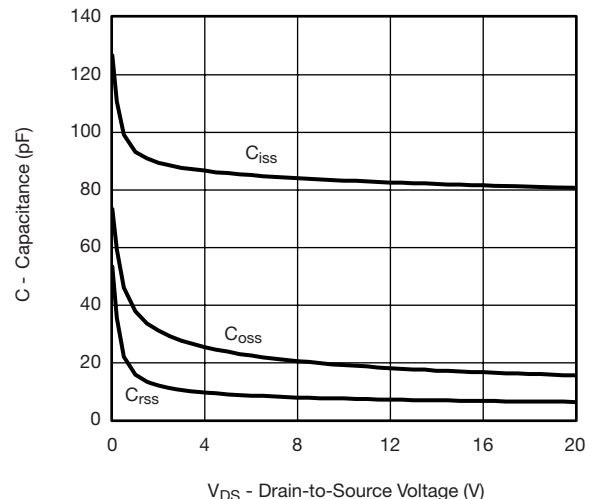
Output Characteristics



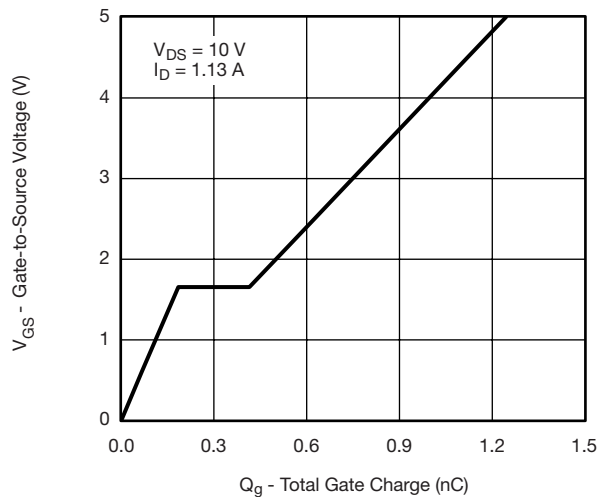
Transfer Characteristics



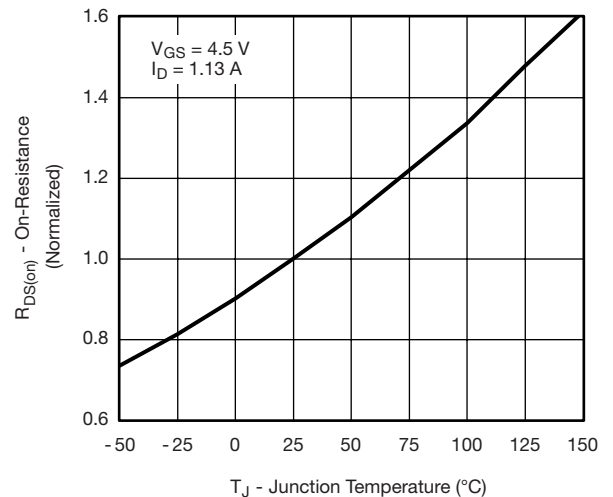
On-Resistance vs. Drain Current



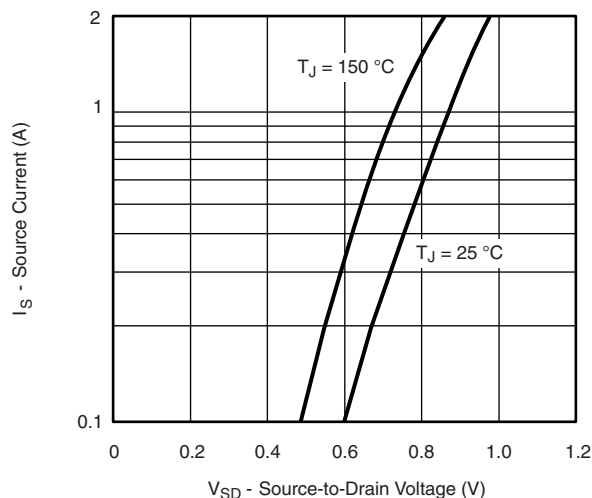
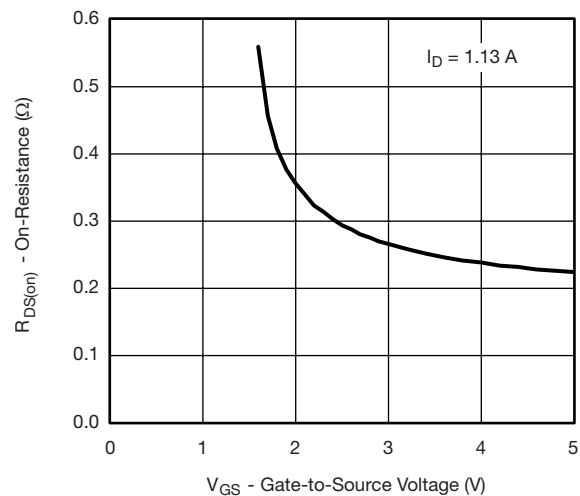
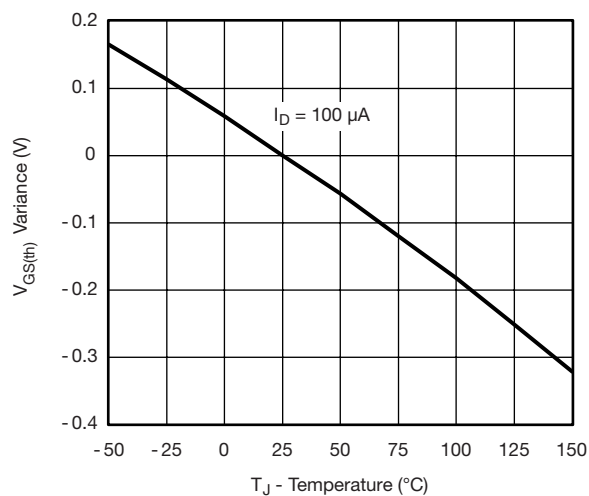
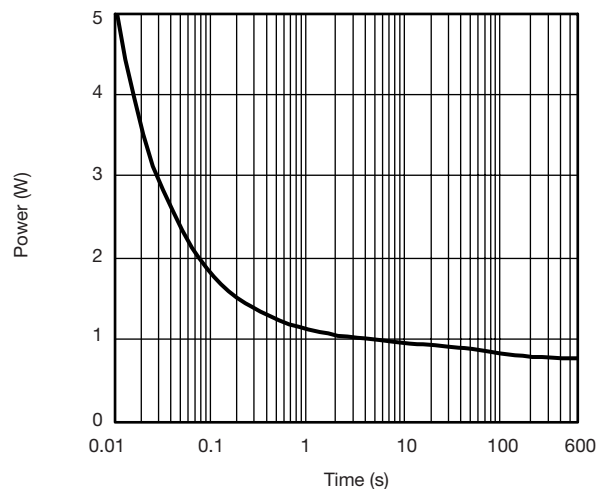
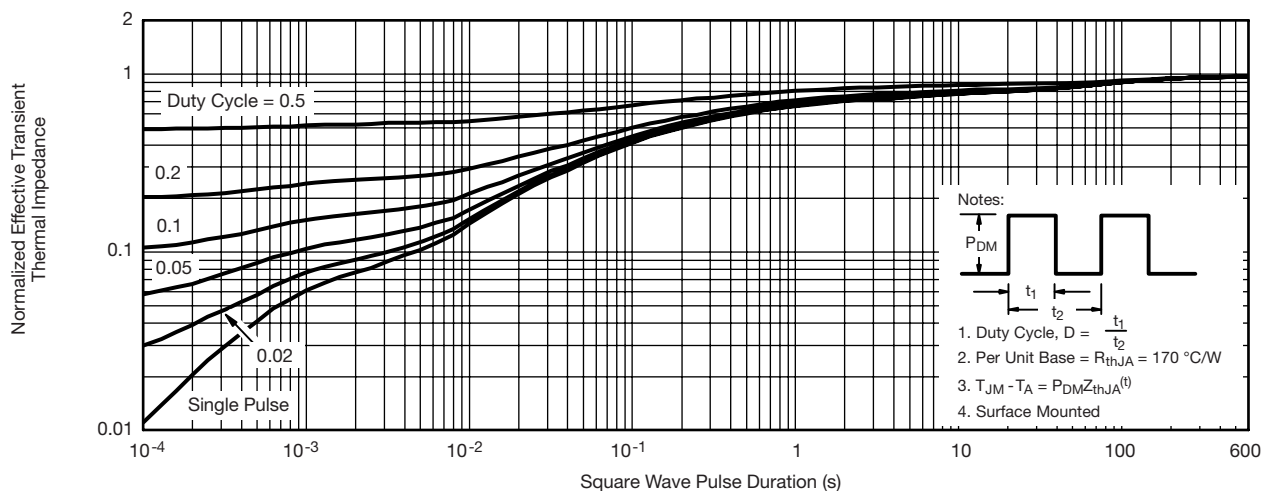
Capacitance



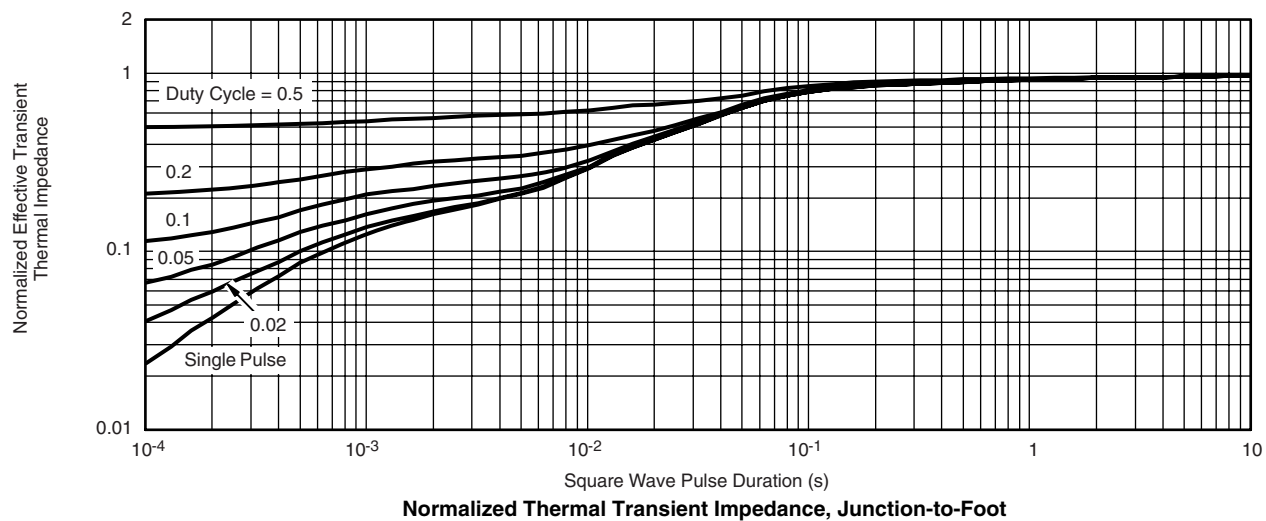
Gate Charge



On-Resistance vs. Junction Temperature

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Ambient**

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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